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Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Amend the claim set, replacing all prior versions, without prejudice or disclaimer of the subject matter thereof, as detailed in the following complete listing of all claims:

1. (Currently amended) A method of manufacturing an integrated circuit carrier (10), the method including the steps of

providing a substrate (46);

demarcating at least one receiving zone (12) for an integrated circuit (14) on the substrate (46) and a plurality of island-defining portions (16) arranged about said at least one receiving zone (12); and

creating one or more a serpentine members (22) between neighboring island-defining portions (16) by removing material from the substrate (46), thereby reducing thermal strains involving the said island-defining portions (16).

- 2. (Currently amended) The method of claim 1 which includes forming electrical contacts (42) in said at least one receiving zone (12) and forming an electrical terminal (18) in each island-defining portion (16), each electrical terminal (18) being electrically connected via a track (52) of a circuitry layer (48) to one of the electrical contacts (42).
- 3. (Currently amended) The method of claim 2 which includes forming the circuitry layer (48) on a surface of the substrate (46) by depositing a metal layer on the substrate (46).
- 4. (Cancelled)
- (Cancelled)
- 6. (Currently amended) The method of claim 1 which includes creating the <u>one or more serpentine members (22) rigidity-reducing arrangements</u> by etching through the substrate (46).



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- 7. (Currently amended) The method of claim 1 which includes forming the substrate (46) from a wafer of undoped silicon having an insulating layer (54).
- 8. (Currently amended) The method of claim 1 which includes demarcating said at least one receiving zone (12) by forming a recess in the substrate (46).
- 9. (Currently amended) The method of claim 8 which includes forming the recess by etching the substrate (46).
- 10. (Cancelled)
- 11. (Cancelled)

